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Docket Number (Optional)	Application Number
SETI-0001	09/966563
Applicant(s)	
Khan et al.	
Filing Date	**Group Art Unit**
September 27, 2001	2814

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		"The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structure," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739.
		"Pyroelectricity in Gallium Nitride Thin Films," A. D. Bykhovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256.

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		"Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.
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